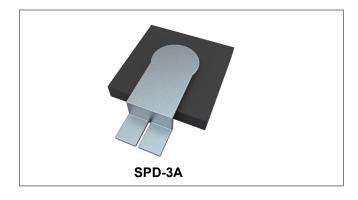






# Power Surface Mount Schottky Rectifier (45V, 120Amp)



### **Features**

- 175 °C T<sub>J</sub> operation
- Low forward voltage drop
- Low reverse leakage current
- · High surge capacities
- High frequency operation
- Guaranteed reverse avalanche capability
- Low profile surface mount package
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

# **Schematic & Pin Configuration**



# **Applications**

- Switching power supply
- Redundant power subsystems
- Reverse battery protection
- Converters
- Many other high current AC/DC power supplies

### **Maximum Ratings:**

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	-	45	V
Average Rectified Forward Current	I <sub>F (AV)</sub>	50% duty cycle @T <sub>C</sub> =116°C, rectangular wave form	120	А
Peak One Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	8.3 ms, half Sine pulse	1650	Α
Non-Repetitive Avalanche Energy	E <sub>AS</sub>	T <sub>J</sub> =25℃,I <sub>AS</sub> =11A, L=1.2mH	76	mJ
Repetitive Avalanche Current	I <sub>AR</sub>	$I_{AS}$ decaying linearly to 0 in 1 $\mu$ sec Frequency limited by $T_J$ max. $V_A$ =1.5 $\times V_R$	11	А

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# **Electrical Characteristics:**

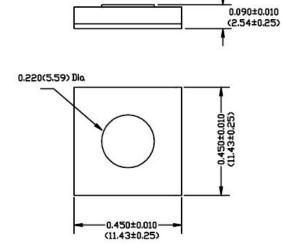
Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop *	V <sub>F1</sub>	@ 120A, Pulse, T <sub>J</sub> = 25 °C	0.58	0.66	V
	V <sub>F2</sub>	@ 120A, Pulse, T <sub>J</sub> = 125 °C	0.53	0.59	V
Reverse Current*	I <sub>R1</sub>	$@V_R = \text{rated } V_R, \text{ Pulse}, \\ T_J = 25  ^{\circ}\text{C}$	0.06	2.4	mA
	I <sub>R2</sub>	$@V_R = \text{rated } V_R, \text{ Pulse}, \\ T_J = 125  ^{\circ}\text{C}$	10	90	mA
Junction Capacitance	Ст	$@V_R = 5V, T_C = 25 \text{ °C}$ $f_{SIG} = 1MHz$	4200	4800	pF
Voltage Rate of Change	dv/dt	-	-	10,000	V/μs

<sup>\*</sup> Pulse width < 300 µs, duty cycle < 2%

# **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T <sub>stg</sub>	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case	R <sub>θ</sub> JC	DC operation	0.20	°C/W

### **Mechanical Dimensions (Inches/Millimeters)**



0.015 0.105±0.010 (0.38) (2.67±0.25) 0.040 (1.02) 0.135 (3.43) 0.050 (3.43) 0.050 (3.43) 0.050 (3.43)

SPD-3A

# **Suffix "R" Denotes Reversed Polarity**

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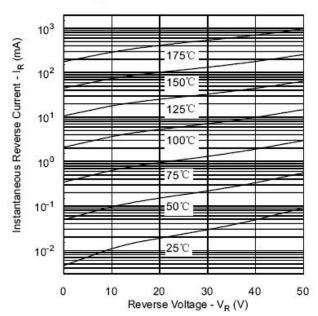


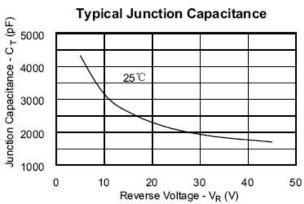
# **Ratings and Characteristics Curves**

### **Typical Forward Characteristics**

# 10<sup>2</sup> 10<sup>2</sup> 10<sup>3</sup> 10<sup>4</sup> 10<sup>5</sup> 125°C 125°C 125°C 0.2 0.3 0.4 0.5 0.6 0.7 0.8 Forward Voltage Drop - V<sub>F</sub> (V)

### Typical Reverse Characteristics





# **Ordering Information**

Device	Package	Shipping	
121SPC045(A)	SPD-3A(Pb-Free)	100pcs/ box	

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

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